

# New Jersey Semi-Conductor Products, Inc.

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## 2N3733

NPN silicon transistor designed for amplifier, frequency multiplier, and oscillator applications.

### MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Collector-Emitter Voltage (V <sub>EB</sub> (off) = 1.5 Vdc)	V <sub>CEV</sub>	65	Vdc
Collector-Base Voltage	V <sub>CB</sub>	65	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	4.0	Vdc
Collector Current	I <sub>C</sub>	3.0	Amps
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	23 0.13	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C



(TO-60)  
stud isolated from case

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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#### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (1) (I <sub>C</sub> = 0 to 200 mA <sub>dc</sub> , I <sub>B</sub> = 0)	BV <sub>CEO</sub>	40	-	-	Vdc
Collector-Emitter Breakdown Voltage (1) (I <sub>C</sub> = 0 to 200 mA <sub>dc</sub> , V <sub>EB</sub> (off) = 1.5 Vdc)	BV <sub>CEV</sub>	65	-	-	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 0.5 mA <sub>dc</sub> , I <sub>E</sub> = 0)	BV <sub>CBO</sub>	65	-	-	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 0.25 mA <sub>dc</sub> , I <sub>C</sub> = 0)	BV <sub>EBO</sub>	4.0	-	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	0.25	mA <sub>dc</sub>

#### ON CHARACTERISTICS

Collector-Emitter Saturation Voltage (I <sub>C</sub> = 500 mA <sub>dc</sub> , I <sub>B</sub> = 100 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	-	-	1.0	Vdc
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#### DYNAMIC CHARACTERISTICS

Current-Gain - Bandwidth Product (I <sub>C</sub> = 150 mA <sub>dc</sub> , V <sub>CE</sub> = 28 Vdc, f = 100 MHz)	f <sub>T</sub>	-	400	-	MHz
Output Capacitance (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)	C <sub>ob</sub>	-	-	20	pF
Collector-Case Capacitance	C <sub>s</sub>	-	-	6.0	pF
Base-Spreading Resistance (I <sub>C</sub> = 250 mA <sub>dc</sub> , V <sub>CE</sub> = 28 Vdc, f = 200 MHz)	r <sub>bb'</sub>	-	6.5	-	Ohms

#### FUNCTIONAL TEST

Power Output	V <sub>CE</sub> = 28 Vdc, P <sub>in</sub> = 4 W, f = 260 MHz	P <sub>out</sub>	-	14.5	-	Watts
Efficiency		η	-	60	-	%
Power Output	V <sub>CE</sub> = 28 Vdc, P <sub>in</sub> = 4 W, f = 400 MHz (Figure 1)	P <sub>out</sub>	10	-	-	Watts
Efficiency		η	45	-	-	%

(1) Pulsed through a 25-Ω inductor; duty cycle = 50%